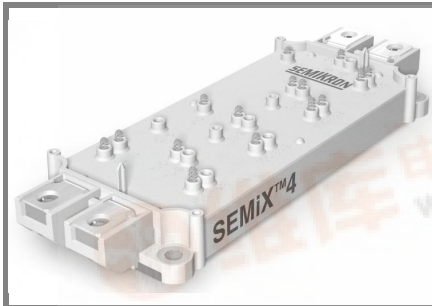


SEMIX 854GB176HDS



SEMIX[®] 4s

Trench IGBT Modules

SEMIX 854GB176HDS

Target Data

Features

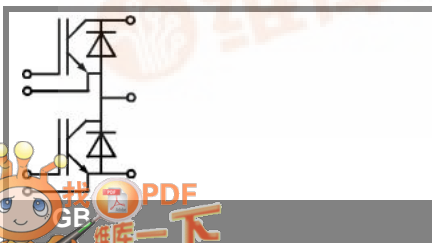
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

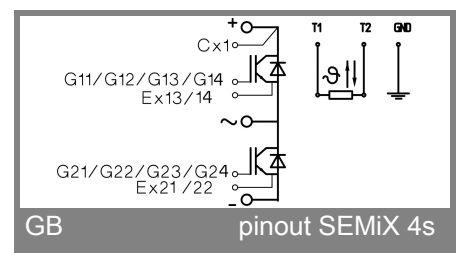
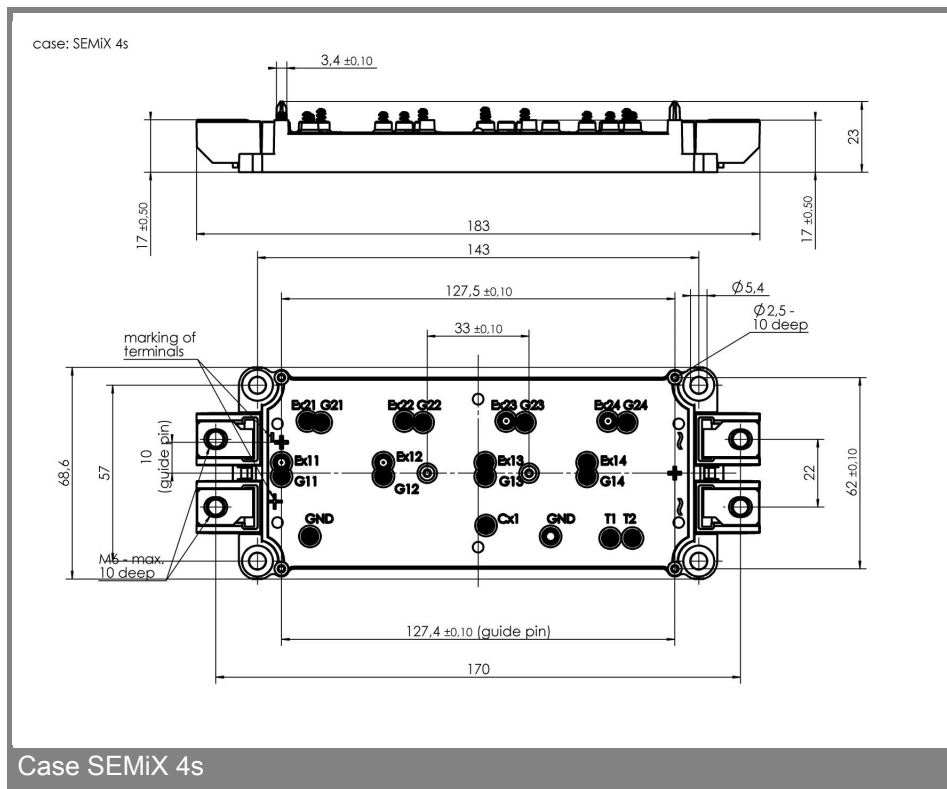
- AC inverter drives
- UPS
- Electronic welders

Absolute Maximum Ratings		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}		1700		V
I_C	$T_c = 25\text{ (80) }^\circ\text{C}$	830 (590)		A
I_{CRM}	$t_p = 1\text{ ms}$	1200		A
V_{GES}		± 20		V
T_{vj} , (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)		$^\circ\text{C}$
V_{isol}	AC, 1 min.	4000		V
Inverse diode				
I_F	$T_c = 25\text{ (80) }^\circ\text{C}$	590 (370)		A
I_{FRM}	$t_p = 1\text{ ms}$	1200		A
I_{FSM}	$t_p = 10\text{ ms}$; sin.; $T_j = 25\text{ }^\circ\text{C}$	1550		A

Characteristics		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 24\text{ mA}$	5,2	5,8	6,4	V
I_{CES}	$V_{GE} = 0$, $V_{CE} = V_{CES}$, $T_j = 25\text{ (125) }^\circ\text{C}$			3,6	mA
$V_{CE(TO)}$	$T_j = 25\text{ (125) }^\circ\text{C}$		1 (0,9)	1,2 (1,1)	V
r_{CE}	$V_{GE} = 0\text{ V}$, $T_j = 25\text{ (125) }^\circ\text{C}$		1,7 (2,6)	2,1 (3)	m Ω
$V_{CE(sat)}$	$I_{Cnom} = 600\text{ A}$, $V_{GE} = 15\text{ V}$, $T_j = 25\text{ (125) }^\circ\text{C}$, chip level		2 (2,45)	2,45 (2,9)	V
C_{ies}	under following conditions		39,6		nF
C_{oes}	$V_{GE} = 0$, $V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$		2,2		nF
C_{res}			1,8		nF
L_{CE}			22		nH
R_{CC+EE}	terminal-chip, $T_c = 25\text{ (125) }^\circ\text{C}$				m Ω
$t_{d(on)}/t_r$	$V_{CC} = 1200\text{ V}$, $I_{Cnom} = 600\text{ A}$		410 / 70		ns
$t_{d(off)}/t_f$	$V_{GE} = \pm 15\text{ V}$		775 / 145		ns
$E_{on} (E_{off})$	$R_{Gon} = R_{Goff} = 1\text{ }^\Omega$, $T_j = 125\text{ }^\circ\text{C}$		298 (202)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_{Fnom} = 600\text{ A}$; $V_{GE} = 0\text{ V}$; $T_j = 25\text{ (125) }^\circ\text{C}$, chip level		2 (2,1)	2,2 (2,3)	V
$V_{(TO)}$	$T_j = 25\text{ (125) }^\circ\text{C}$		1,1 (0,9)	1,3 (1,1)	V
r_T	$T_j = 25\text{ (125) }^\circ\text{C}$		1,5 (2)	1,5 (2)	m Ω
I_{RRM}	$I_{Fnom} = 600\text{ A}$; $T_j = 25\text{ (125) }^\circ\text{C}$		(825)		A
Q_{rr}	$di/dt = 10000\text{ A}/\mu\text{s}$		(230)		μC
E_{rr}	$V_{GE} = -15\text{ V}$		(172)		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,039	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,09	K/W
$R_{th(j-c)FD}$	per FWD				K/W
$R_{th(c-s)}$	per module		0,03		K/W
Temperature sensor					
R_{25}	$T_c = 25\text{ }^\circ\text{C}$		5 \pm 5%		k Ω
$B_{25/85}$	$R_2 = R_1 \exp[B(1/T_2 - 1/T_1)]$; $T[K]; B$		3420		K
Mechanical data					
M_s/M_t	to heatsink (M5) / for terminals (M6)	3/2,5		5 / 5	Nm
w			390		g



SEMiX 854GB176HDs



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.